

80-103 as follows:

--80. A multi-chamber system comprising:

a first chamber for irradiating laser light to a semiconductor film formed over a substrate;

a second chamber for depositing a gate insulating film on said semiconductor film; and

~~or~~ a third chamber capable of taking said substrate out of said multi-chamber system after depositing said gate insulating film.

81. A multi-chamber system according to claim 80 wherein said second chamber is selected from apparatuses consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a sputtering film formation apparatus.

82. A multi-chamber system according to claim 81 wherein said apparatuses are capable of forming a silicon oxide film.

83. A multi-chamber system comprising:

a first chamber for irradiating laser light to a semiconductor film formed over a substrate;

a second chamber for performing at least one heating process;

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a third chamber for depositing a gate insulating film on said semiconductor film; and

a fourth chamber capable of taking said substrate out of said multi-chamber system after depositing said gate insulating film.

84. A multi-chamber system according to claim 83 wherein said third chamber is selected from apparatuses consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a sputtering film formation apparatus.

85. A multi-chamber system according to claim 84 wherein said ~~apparatuses are capable of forming a silicon oxide film.~~

86. A multi-chamber system comprising:

a first chamber for irradiating laser light to a semiconductor film formed over a substrate;

a second chamber for depositing a gate insulating film on said semiconductor film;

a third chamber capable of taking said substrate out of said multi-chamber system after depositing said gate insulating film; and

a means for transporting said substrate among said first, second and third chambers.

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87. A multi-chamber system according to claim 86 wherein said second chamber is selected from apparatuses consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a sputtering film formation apparatus.

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88. A multi-chamber system according to claim 87 wherein said apparatuses are capable of forming a silicon oxide film.

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89. A multi-chamber system comprising:  
a first chamber for irradiating laser light to a semiconductor film formed over a substrate;  
a second chamber for performing at least one heating process;  
a third chamber for depositing a gate insulating film on said semiconductor film;  
a fourth chamber capable of taking said substrate out of said multi-chamber system after depositing said gate insulating film;  
a means for transporting said substrate among said first, second, third and fourth chambers.

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90. A multi-chamber system according to claim 89 wherein said third chamber is selected from apparatuses consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a

~~sputtering film formation apparatus.~~

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91. A multi-chamber system according to claim 90 wherein said apparatuses are capable of forming a silicon oxide film.

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92. A multi-chamber system comprising:  
a first chamber for irradiating laser light to a semiconductor film formed over a substrate;  
a second chamber for depositing a gate insulating film; and  
a third chamber for putting said substrate in said multi-chamber system and for taking said substrate out of said multi-chamber system,  
wherein said multi-chamber system is capable of depositing said gate insulating film on said semiconductor film irradiated with said laser light.

93. A multi-chamber system according to claim 92 wherein said second chamber is selected from apparatuses consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a sputtering film formation apparatus.

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94. A multi-chamber system according to claim 93 wherein said apparatuses are capable of forming a silicon oxide film.

95. A multi-chamber system comprising:

a first chamber for irradiating laser light to a semiconductor film formed over a substrate;

a second chamber for performing at least one heating process;

a third chamber for depositing a gate insulating film; and

a fourth chamber for putting said substrate in said multi-chamber system and for taking said substrate out of said multi-chamber system,

wherein said multi-chamber system is capable of depositing said gate insulating film on said semiconductor film irradiated with said laser light.

96. A multi-chamber system according to claim 95 wherein said third chamber is selected from apparatuses consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a sputtering film formation apparatus.

97. A multi-chamber system according to claim 96 wherein said apparatuses are capable of forming a silicon oxide film.

98. A multi-chamber system comprising:

a first chamber for irradiating laser light to a semiconductor film formed over a substrate;

a second chamber for depositing a gate insulating film;

a third chamber for putting said substrate in said multi-chamber system and for taking said substrate out of said multi-chamber system; and

a means for transporting said substrate among said first, second and third chambers,

wherein said multi-chamber system is capable of depositing said gate insulating film on said semiconductor film irradiated with said laser light.

99. A multi-chamber system according to claim 98 wherein said second chamber is selected from apparatuses consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a sputtering film formation apparatus.

100. A multi-chamber system according to claim 99 wherein said apparatuses are capable of forming a silicon oxide film.

101. A multi-chamber system comprising:  
a first chamber for irradiating laser light to a semiconductor film formed over a substrate;

a second chamber for performing at least one heating process;

a third chamber for depositing a gate insulating film;

a fourth chamber for putting said substrate in said multi-chamber system and for taking said substrate out of said multi-chamber system; and

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